



ACE1550B

P-Channel Enhancement Mode Field Effect Transistor

Description

The ACE1550B combines advanced trench MOSFET technology with a low resistance package to provide This device is ideal for Power Supply Converter Circuits and Load/Power Switching Cell Phones, Pagers.

Features

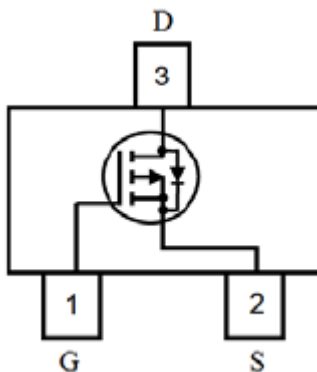
- $V_{DS}(V) = -20V$
- $I_D = -0.7A$
- $R_{DS(ON)} < 620m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 860m\Omega$ ($V_{GS} = -2.5V$)
- $R_{DS(ON)} < 1450m\Omega$ ($V_{GS} = -1.8V$)

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit	
Drain-Source Voltage	V_{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	± 12	V	
Continuous Drain Current * AC	I_D	$T_A = 25^\circ C$	-0.7	A
		$T_A = 70^\circ C$	-0.56	
Pulsed Drain Current * B	I_{DM}	-1	A	
Power Dissipation	P_D	$T_A = 25^\circ C$	0.27	W
		$T_A = 70^\circ C$	0.16	
Operating Junction Temperature / Storage Temperature Range	T_J/T_{STG}	-55/150	$^\circ C$	

Packaging Type

SOT-523



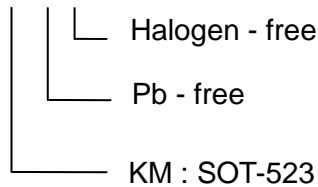


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Ordering information

ACE1550B XX + H



Electrical Characteristics

$T_A=25^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\text{ uA}$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=-250\text{ uA}$	-0.3		-0.8	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			1	μA
Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-0.6A$		500	620	m Ω
		$V_{GS}=-2.5V, I_D=-0.5A$		700	860	
		$V_{GS}=-1.8V, I_D=-0.4A$		1000	1450	
Forward Transconductance	gfs	$V_{DS}=-10V, I_D=-0.4A$		1		S
Diode Forward Voltage	V_{SD}	$I_{SD}=-0.15A, V_{GS}=0V$		-0.65	-1.2	V
Switching						
Total Gate Charge	Q_g	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-0.25A$		1.0	1.3	nC
Gate-Source Charge	Q_{gs}			0.1		
Gate-Drain Charge	Q_{gd}			0.3		
Turn-On Time	td(on)	$V_{GS}=-4.5V, I_D=-0.2A, V_{DS}=-10V, R_G=10\Omega$		10	15	nS
	tr			10	15	
Turn-Off Time	td(off)			40	60	
	tf			30	50	
Dynamic						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=-10V, f=1\text{MHz}$		70	100	pF
Output Capacitance	C_{oss}			20		
REVERSE Transfer Capacitance	C_{rss}			10		



Note:

1. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design.
2. Repetitive rating, pulse width limited by junction temperature.
3. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JA}$ and lead to ambient .
4. The static characteristics are obtained using $<300\ \mu\text{s}$ pulses, duty cycle 0.5% max.
5. These tests are performed with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

Typical Performance Characteristics

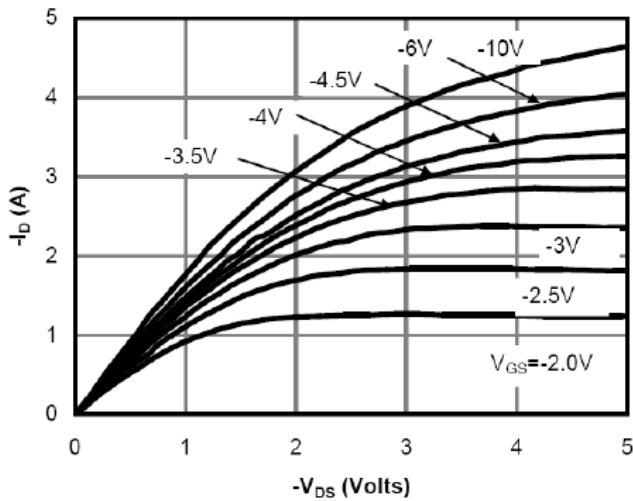


Figure 1: On-Region Characteristics

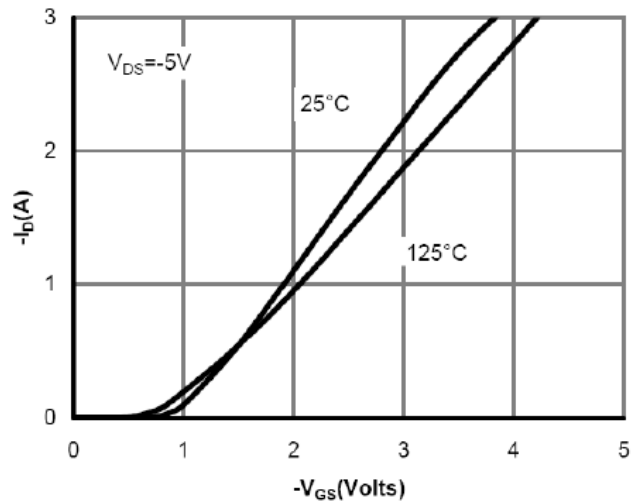


Figure 2: Transfer Characteristics

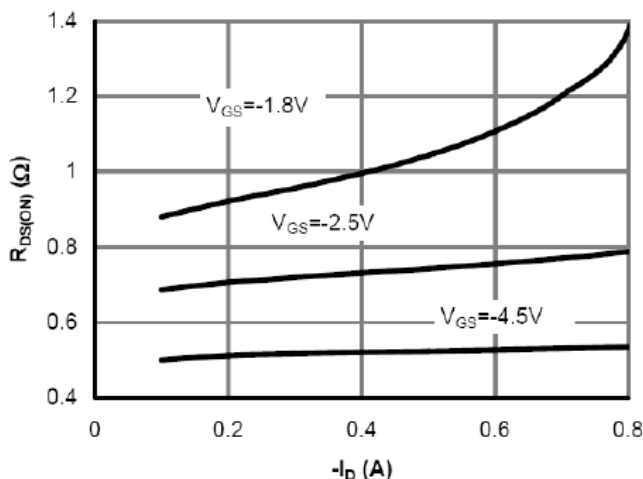


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

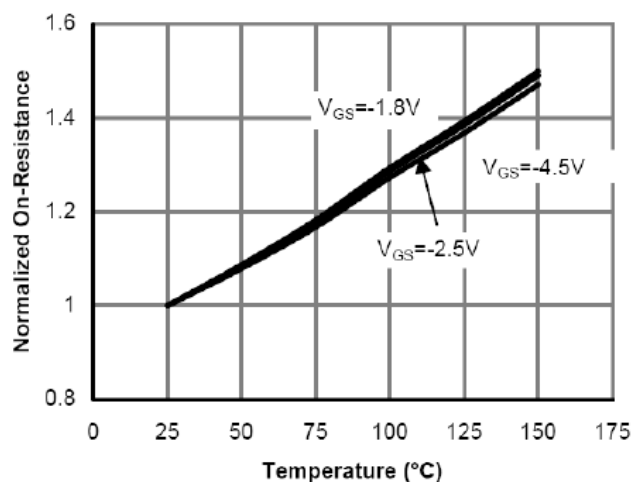


Figure 4: On-Resistance vs. Junction Temperature



Typical Performance Characteristics

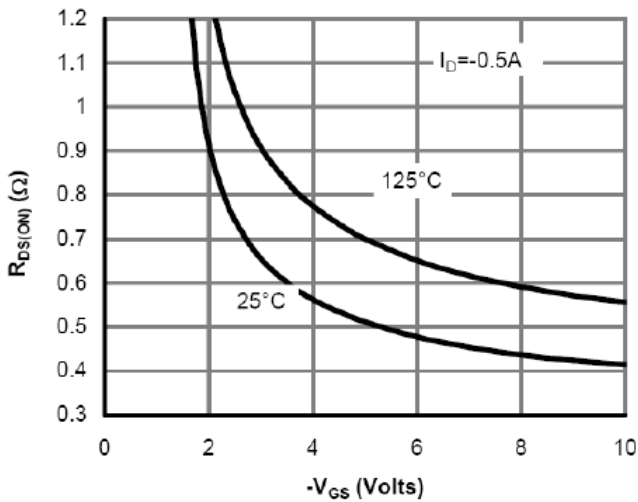


Figure 5: On-Resistance vs. Gate-Source Voltage

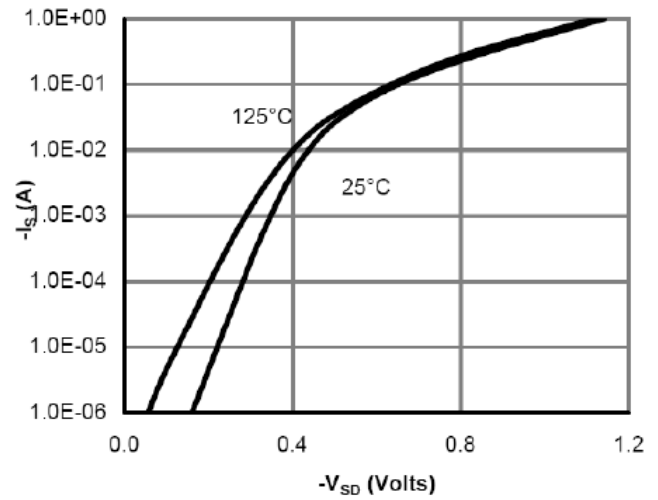


Figure 6: Body-Diode Characteristics

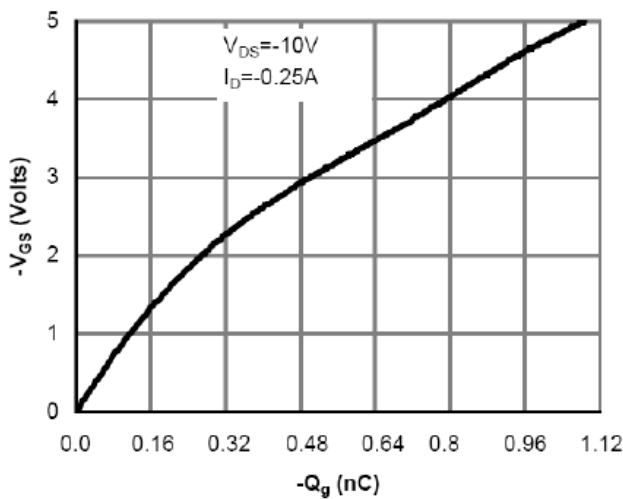


Figure 7: Gate-Charge Characteristics

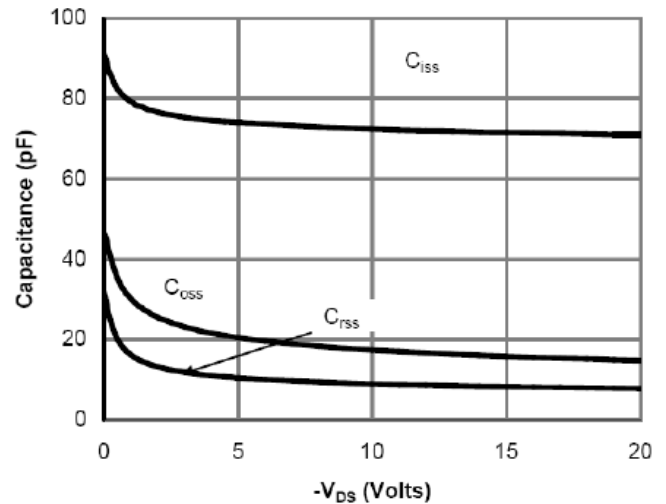


Figure 8: Capacitance Characteristics

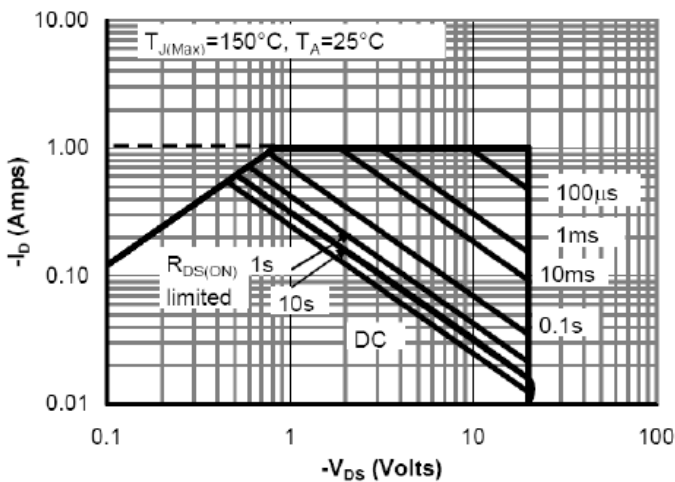


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

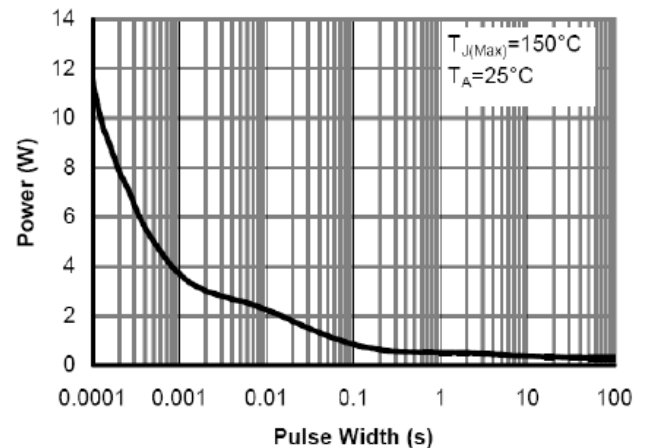


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)



Typical Performance Characteristics

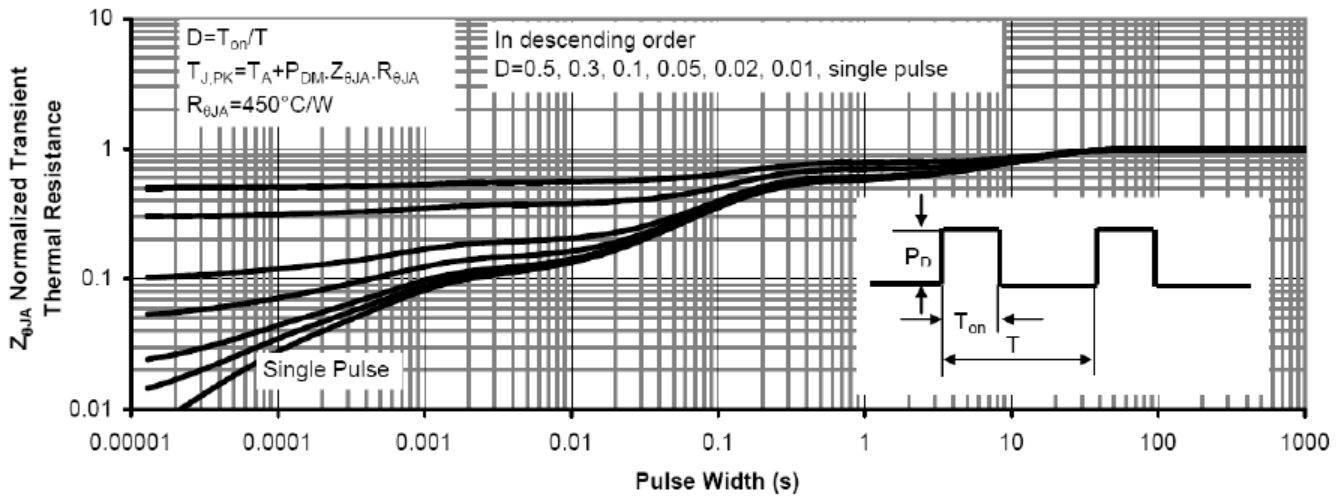


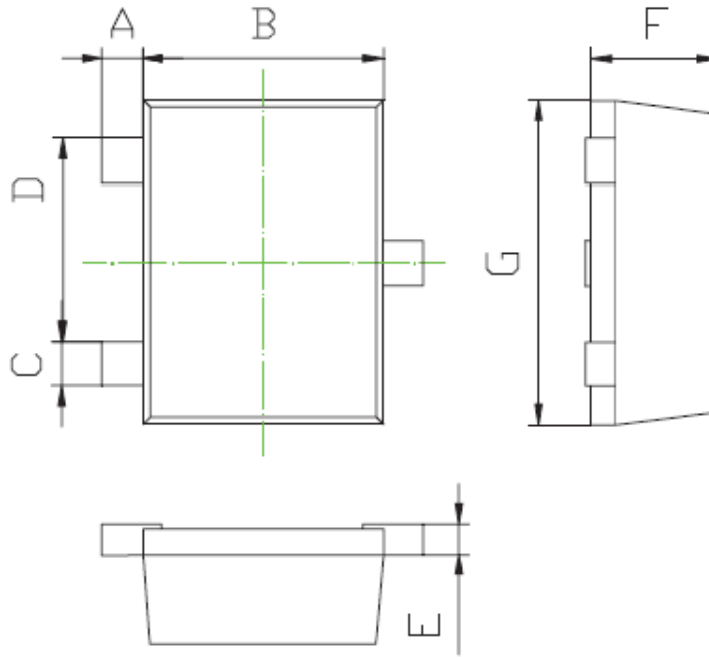
Figure 11: Normalized Maximum Transient Thermal Impedance



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Packing Information

SOT-523



Unit:mm			
Dim.	Min.	Typ.	Max.
A	0.1	0.2	0.3
B	1.10	1.20	1.30
C	0.17	0.22	0.27
D	0.95	1.00	1.05
E	0.09	0.125	0.16
F	0.525	0.575	0.60
G	1.5	1.6	1.7



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+Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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